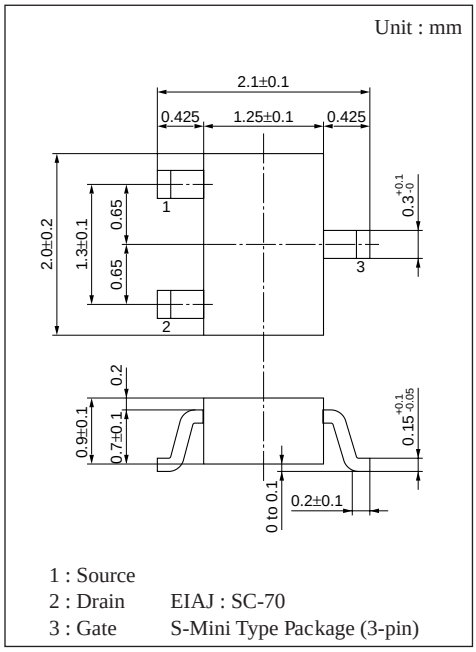
2SK662

Silicon N-Channel Junction

For low-frequency amplification



■ Features

- High mutual conductance g_m
- Low noise type
- Downsizing of sets by S-mini type package and automatic insertion by taping/magazine packing are available.

■ Absolute Maximum Ratings (Ta = 25˚C)

Parameter	Symbol	Rating	Unit
Drain-Source voltage	V_{DSX}	30	V
Gate-Drain voltage	V_{GDO}	– 30	V
Drain current	I_D	± 20	mA
Gate current	I_G	10	mA
Allowable power dissipation	P_D	150	mW
Junction temperature	T_j	125	˚C
Storage temperature	T_{stg}	–55 to +125	˚C

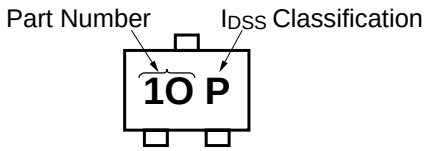
■ Electrical Characteristics (Ta = 25˚C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I_{DSS} *	V_{DS}=10V, V_{GS}= 0	0.5		12	mA
Gate-Source leakage current	I_{GSS}	V_{GS}= ± 30V, V_{DS}= 0			–100	nA
Gate-Source cut-off voltage	V_{GSC}	V_{DS}=10V, I_D=10µA	– 0.1		–1.5	V
Mutual conductance	g_m	V_{DS}=10V, I_D= 0.5mA, f=1kHz	4			mS
		V_{DS}=10V, V_{GS}= 0, f=1kHz	4			
Input capacitance	C_{iss}	V_{DS}=10V, V_{GS}= 0, f=1MHz		14		pF
Feedback capacitance	C_{rss}			3.5		pF
Noise voltage	NV	V_{DS}= 30V, I_D=1mA, G_V= 80dB R_g=100kΩ, Function= FLAT		60		mV

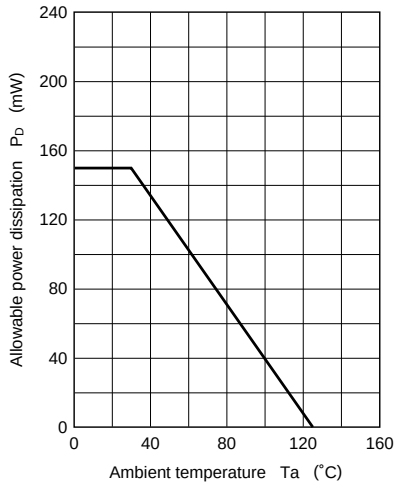
* I_{DSS} rank classification

Rank	P	Q	R
I_{DSS}(mA)	0.5 to 3	2 to 6	4 to 12
Part number symbol	1OP	1OQ	1OR

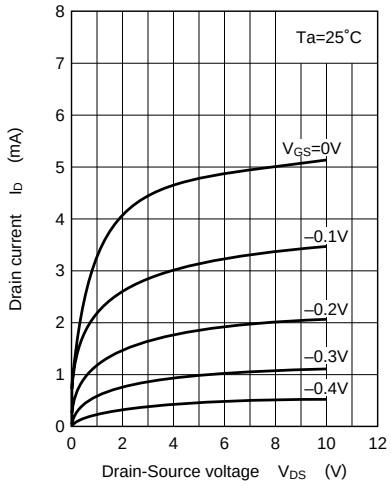
■ Marking (Example)



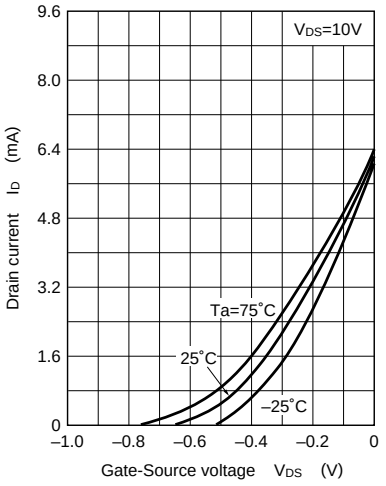
$P_D - Ta$



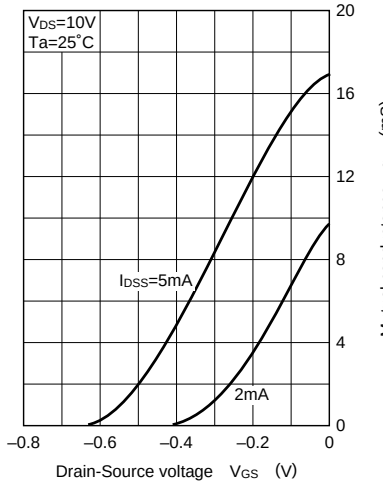
$I_D - V_{DS}$



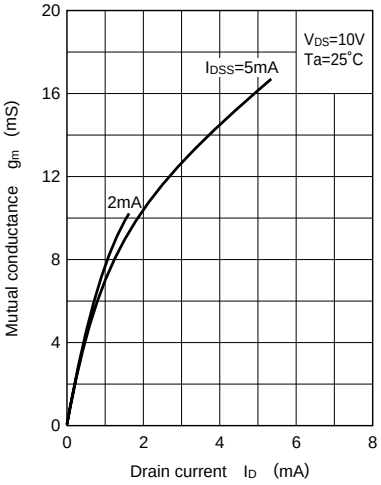
$I_D - V_{GS}$



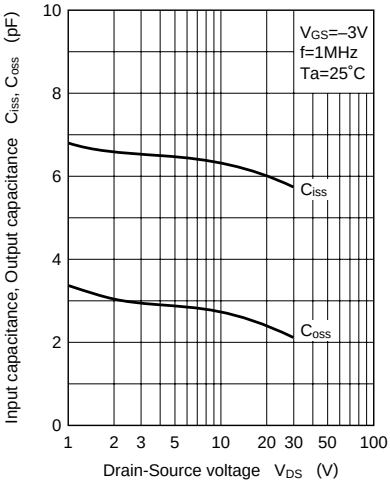
$g_m - V_{GS}$



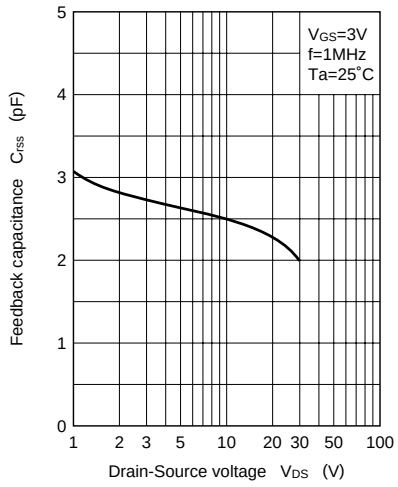
$g_m - I_D$



$C_{iss}, C_{oss} - V_{DS}$



$C_{rss} - V_{DS}$



$NF - f$